Preferred Devices

# Product Preview

# **Complementary PNP-NPN Silicon Power Transistors**

The MJL31193 and MJL31194 are PowerBase<sup>™</sup> transistors that are specifically designed for high power audio output.

#### **Features**

- High DC Current Gain h<sub>FE</sub> = 25 Min @ I<sub>C</sub> = 10 A
- Excellent Gain Linearity
- Low Harmonic Distortion
- Ultra High Safe Operation Area

## **MAXIMUM RATINGS** ( $T_J = 25^{\circ}C$ unless otherwise noted)

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	V <sub>CEO</sub>	250	Vdc
Collector-Base Voltage	V <sub>CBO</sub>	400	Vdc
Emitter-Base Voltage	V <sub>EBO</sub>	5.0	Vdc
Collector–Emitter Voltage – 1.5 V	V <sub>CEX</sub>	400	Vdc
Collector Current – Continuous – Peak (Note 1)	I <sub>C</sub>	20 40	Adc
Base Current – Continuous	Ι <sub>Β</sub>	5.0	Adc
Total Power Dissipation @ T <sub>C</sub> = 25°C Derate Above 25°C	P <sub>D</sub>	250 1.84	Watts W/°C
Operating and Storage Junction Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	- 65 to +150	°C

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	0.50	°C/W

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

1. Pulse Test: Pulse Width = 5 μs, Duty Cycle ≤ 10%.



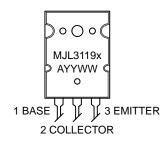
ON Semiconductor®

http://onsemi.com

20 AMPERE
COMPLEMENTARY
SILICON POWER
TRANSISTORS
250 VOLTS
250 WATTS



#### **MARKING DIAGRAM**



x = 3 or 4
A = Location Code
YY = Year
WW = Work Week

#### **ORDERING INFORMATION**

Device	Package	Shipping	
MJL31193	TO-264	30 Units/Rail	
MJL31194	TO-264	30 Units/Rail	

**Preferred** devices are recommended choices for future use and best overall value.

This document contains information on a product under development. ON Semiconductor reserves the right to change or discontinue this product without notice.

## **ELECTRICAL CHARACTERISTICS** (T<sub>C</sub> = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Typical	Max	Unit
OFF CHARACTERISTICS						
Collector–Emitter Sustaining Voltage (I <sub>C</sub> = 100 mAdc, I <sub>B</sub> = 0 Adc)		V <sub>CEO(sus)</sub>	250	-	-	Vdc
Collector Cutoff Current (V <sub>CE</sub> = 200 Vdc, I <sub>B</sub> = 0 Adc)		I <sub>CEO</sub>	-	-	100	μAdc
Emitter Cutoff Current (V <sub>CE</sub> = 5.0 Vdc, I <sub>C</sub> = 0 Adc)		I <sub>EBO</sub>	-	-	10	μAdc
Collector Cutoff Current (V <sub>CE</sub> = 250 Vdc, V <sub>BE(off)</sub> = 1.5 Vdc)		I <sub>CEX</sub>	-	-	50	μAdc
ON CHARACTERISTICS		•		•	•	•
DC Current Gain ( $I_C = 10$ Adc, $V_{CE} = 5.0$ Vdc) ( $I_C = 20$ Adc, $I_B = 5.0$ Adc)		h <sub>FE</sub>	25 10	_ _	75 -	
Base–Emitter On Voltage ( $I_C = 10$ Adc, $V_{CE} = 5.0$ Vdc)		V <sub>BE(on)</sub>	-	-	1.8	Vdc
Collector–Emitter Saturation Voltage (I <sub>C</sub> = 10 Adc, I <sub>B</sub> = 1.0 Adc)		V <sub>CE(sat)</sub>	-	-	1.2	Vdc
DYNAMIC CHARACTERISTICS						
Total Harmonic Distortion at the Output $V_{RMS} = 28.3 \text{ V}, f = 1 \text{ kHz}, P_{LOAD} = 100 \text{ W}_{RMS}$	h <sub>FE</sub> unmatched	T <sub>HD</sub>	_	0.8	_	%
(Matched pair h <sub>FE</sub> = 50 @ 5 A/5 V)	h <sub>FE</sub> matched		_	0.08	_	
Current Gain Bandwidth Product (I <sub>C</sub> = 1.0 Adc, V <sub>CE</sub> = 10 Vdc, f <sub>test</sub> = 1.0 MHz)		f <sub>T</sub>	4.0	-	-	MHz
Output Capacitance (V <sub>CB</sub> = 10 Vdc, I <sub>E</sub> = 0, f <sub>test</sub> = 1.0 MHz)		C <sub>ob</sub>	-	-	700	pF

#### **TYPICAL CHARACTERISTICS**

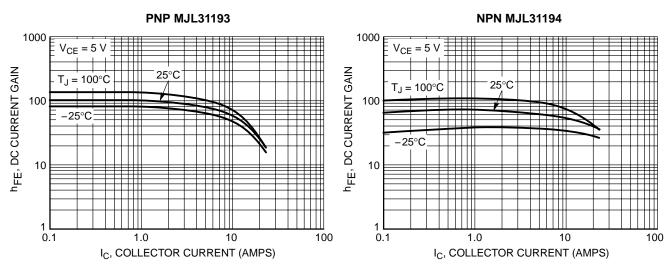


Figure 1. DC Current Gain, V<sub>CE</sub> = 5 V

Figure 2. DC Current Gain, V<sub>CE</sub> = 5 V

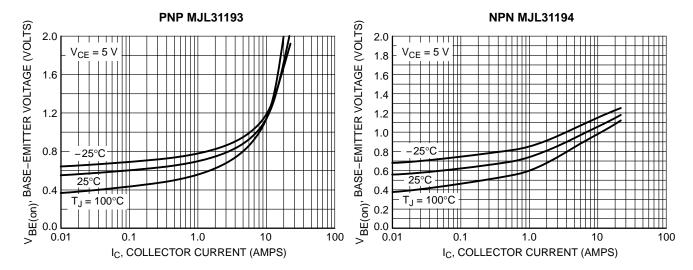
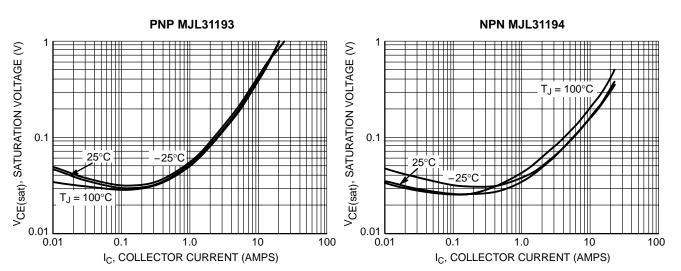


Figure 3. Typical Base-Emitter Voltage



**Figure 5. Typical Saturation Voltages** 

Figure 6. Typical Saturation Voltages

Figure 4. Typical Base-Emitter Voltage

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#### **TYPICAL CHARACTERISTICS**

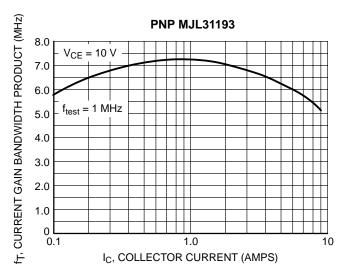


Figure 7. Typical Current Gain Bandwidth Product

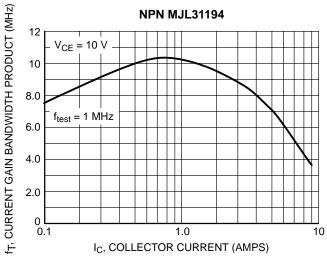


Figure 8. Typical Current Gain Bandwidth Product

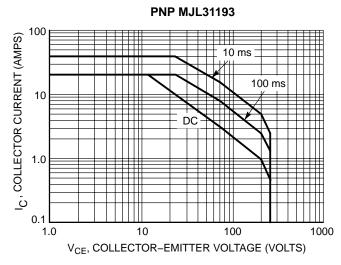


Figure 9. Safe Operating Area

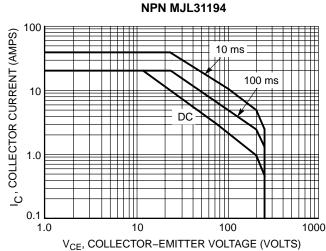


Figure 10. Safe Operating Area

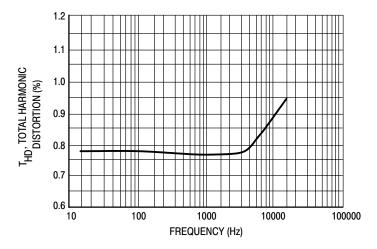


Figure 11. Typical Total Harmonic Distortion

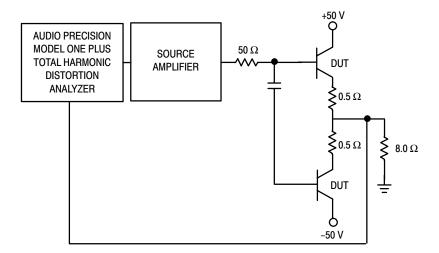
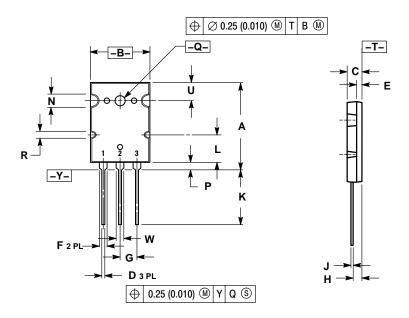


Figure 12. Total Harmonic Distortion Test Circuit

#### PACKAGE DIMENSIONS

TO-3PBL (TO-264) CASE 340G-02 ISSUE H



#### NOTEC.

- DIMENSIONING AND TOLERANCING PER ANSI
   V14 5M 1092
- Y14.5M, 1982. 2. CONTROLLING DIMENSION: MILLIMETER.

	MILLIN	IETERS	INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	28.0	29.0	1.102	1.142	
В	19.3	20.3	0.760	0.800	
С	4.7	5.3	0.185	0.209	
D	0.93	1.48	0.037	0.058	
Е	1.9	2.1	0.075	0.083	
F	2.2	2.4	0.087	0.102	
G	5.45 BSC		0.215 BSC		
Н	2.6	3.0	0.102	0.118	
J	0.43	0.78	0.017	0.031	
K	17.6	18.8	0.693	0.740	
L	11.0	11.4	0.433	0.449	
N	3.95	4.75	0.156	0.187	
P	2.2	2.6	0.087	0.102	
Q	3.1	3.5	0.122	0.137	
R	2.15	2.35	0.085	0.093	
U	6.1	6.5	0.240	0.256	
W	2.8	3.2	0.110	0.125	

STYLE 2: PIN 1. BASE 2 COLL

COLLECTOR
 EMITTER

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